



(51) International Patent Classification:

H01L 21/3205 (2006.01) C23C 16/509 (2006.01)
H01L 21/321 (2006.01) C23C 16/56 (2006.01)
C23C 16/24 (2006.01) H01J 37/32 (2006.01)

(21) International Application Number:

PCT/US2021/048125

(22) International Filing Date:

30 August 2021 (30.08.2021)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

17/014,224 08 September 2020 (08.09.2020) US

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(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

(54) Title: SINGLE CHAMBER FLOWABLE FILM FORMATION AND TREATMENTS

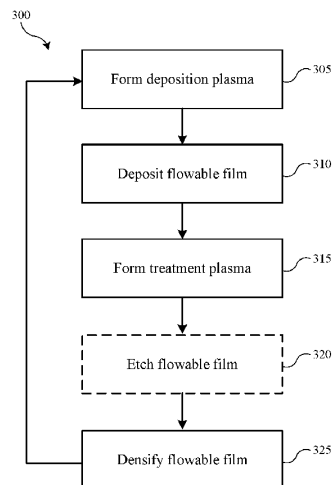


FIG. 3

(57) Abstract: Exemplary processing methods may include forming a plasma of a silicon-containing precursor. The methods may include depositing a flowable film on a semiconductor substrate with plasma effluents of the silicon-containing precursor. The semiconductor substrate may be housed in a processing region of a semiconductor processing chamber. The processing region may be defined between a faceplate and a substrate support on which the semiconductor substrate is seated. The methods may include forming a treatment plasma within the processing region of the semiconductor processing chamber. The treatment plasma may be formed at a first power level from a first power source. A second power may be applied to the substrate support from a second power source at a second power level. The methods may include densifying the flowable film within the feature defined within the semiconductor substrate with plasma effluents of the treatment plasma.

Published:

— with international search report (Art. 21(3))